Silicon NPN Power Transistors 2SD2399

DESCRIPTION

·With TO-220F package
·Complement to type 2SB1568
·High DC current gain.
·DARLINGTON

APPLICATIONS

·For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

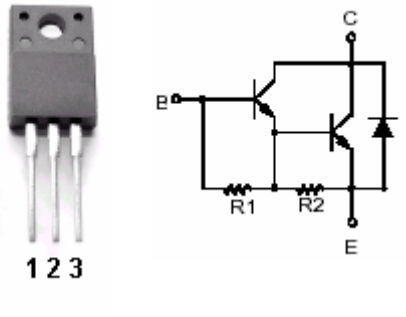


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		4	A
I_{CM}	Collector current-peak	Single pulse	6	A
P_C	Collector dissipation	T_C=25□	30	W
		T_a=25□	2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=50μA; I_E=0	80			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA; I_B=0	80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=2A ; I_B=4mA			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=80V;I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V;I_C=0			3.0	mA
h_{FE}	DC current gain	I_C=2A ; V_{CE}=3V	1000		10000	
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=10V; f=1MHz		35		pF
f_T	Transition frequency	I_E=-0.2A ; V_{CE}=5V;f=10MHz		40		MHz

PACKAGE OUTLINE

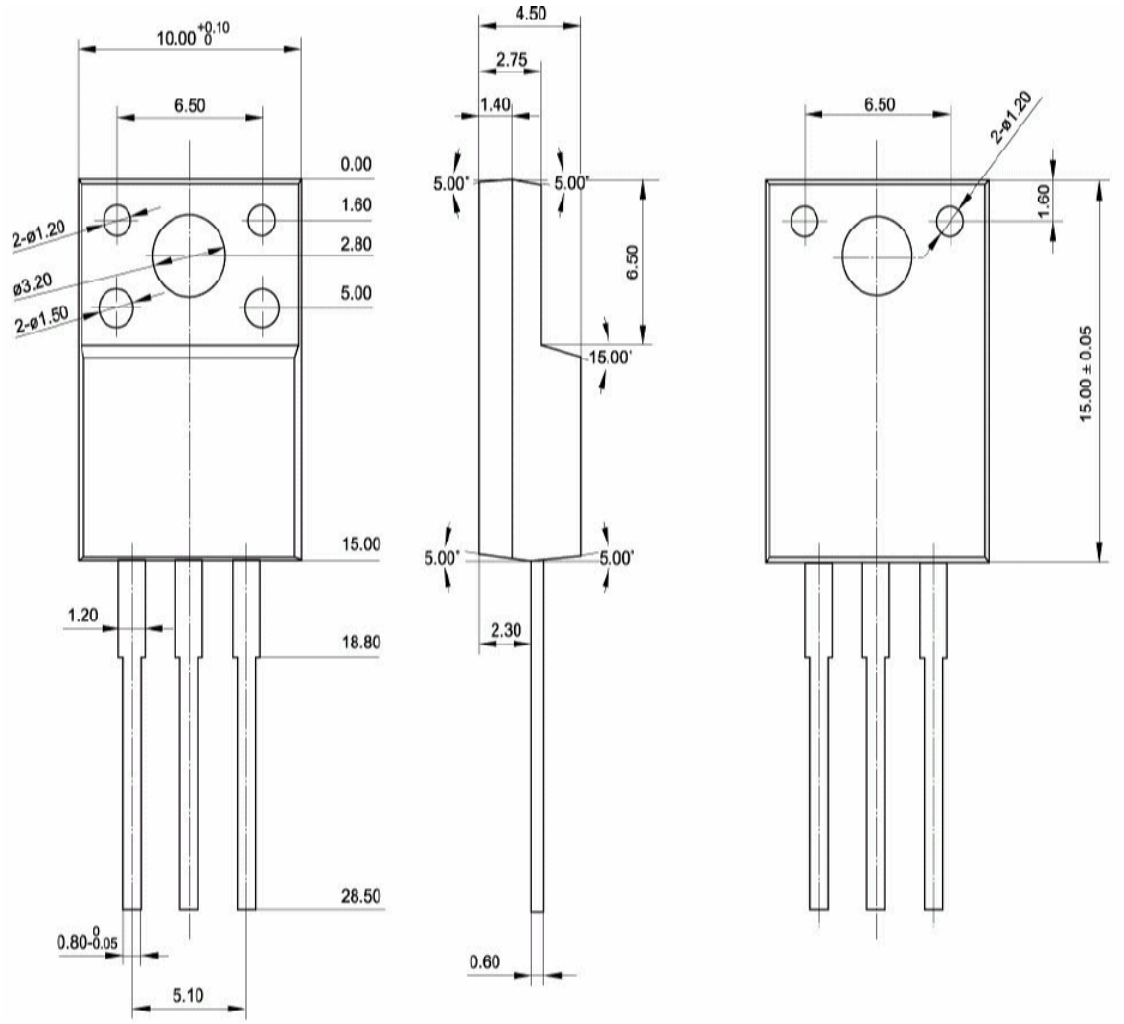


Fig.2 Outline dimensions